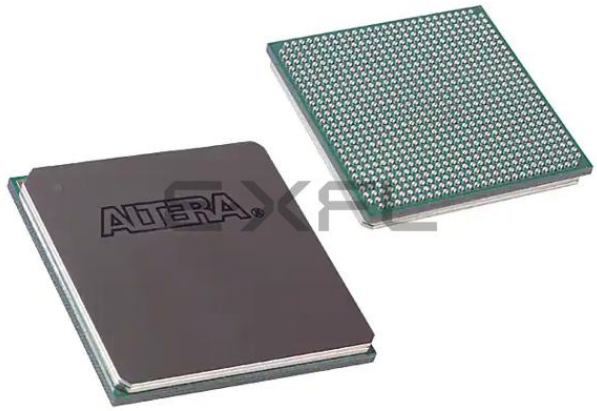

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	1057
Number of Logic Elements/Cells	10570
Total RAM Bits	920448
Number of I/O	426
Number of Gates	-
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	780-BBGA
Supplier Device Package	780-FBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep1s10f780i6n

2. Stratix Architecture

S51002-3.2

Functional Description

Stratix® devices contain a two-dimensional row- and column-based architecture to implement custom logic. A series of column and row interconnects of varying length and speed provide signal interconnects between logic array blocks (LABs), memory block structures, and DSP blocks.

The logic array consists of LABs, with 10 logic elements (LEs) in each LAB. An LE is a small unit of logic providing efficient implementation of user logic functions. LABs are grouped into rows and columns across the device.

M512 RAM blocks are simple dual-port memory blocks with 512 bits plus parity (576 bits). These blocks provide dedicated simple dual-port or single-port memory up to 18-bits wide at up to 318 MHz. M512 blocks are grouped into columns across the device in between certain LABs.

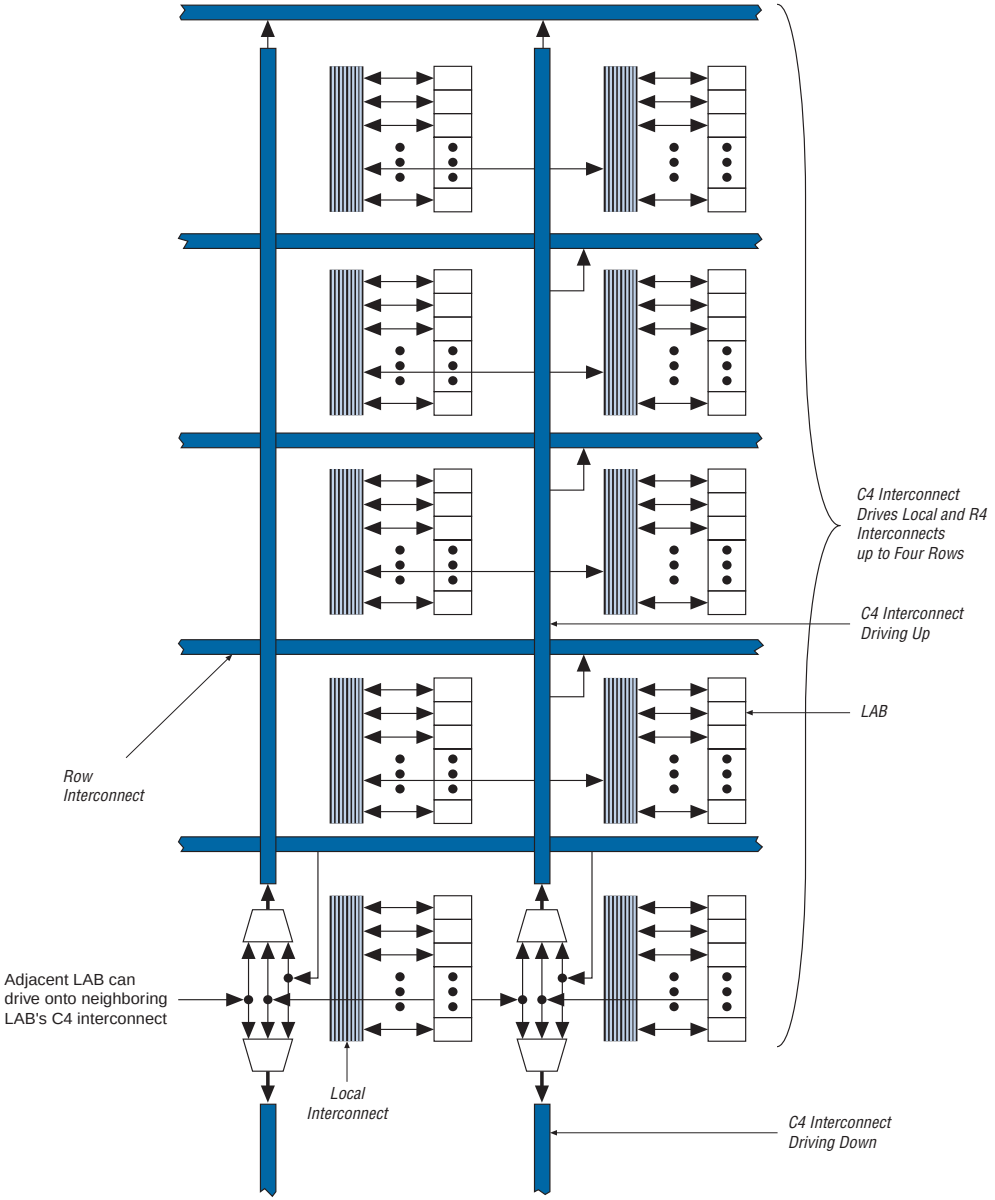
M4K RAM blocks are true dual-port memory blocks with 4K bits plus parity (4,608 bits). These blocks provide dedicated true dual-port, simple dual-port, or single-port memory up to 36-bits wide at up to 291 MHz. These blocks are grouped into columns across the device in between certain LABs.

M-RAM blocks are true dual-port memory blocks with 512K bits plus parity (589,824 bits). These blocks provide dedicated true dual-port, simple dual-port, or single-port memory up to 144-bits wide at up to 269 MHz. Several M-RAM blocks are located individually or in pairs within the device's logic array.

Digital signal processing (DSP) blocks can implement up to either eight full-precision 9 × 9-bit multipliers, four full-precision 18 × 18-bit multipliers, or one full-precision 36 × 36-bit multiplier with add or subtract features. These blocks also contain 18-bit input shift registers for digital signal processing applications, including FIR and infinite impulse response (IIR) filters. DSP blocks are grouped into two columns in each device.

Each Stratix device I/O pin is fed by an I/O element (IOE) located at the end of LAB rows and columns around the periphery of the device. I/O pins support numerous single-ended and differential I/O standards. Each IOE contains a bidirectional I/O buffer and six registers for registering input, output, and output-enable signals. When used with

Figure 2–11. C4 Interconnect Connections Note (1)



Note to Figure 2–11:
(1) Each C4 interconnect can drive either up or down four rows.

M4K RAM blocks support byte writes when the write port has a data width of 16, 18, 32, or 36 bits. The byte enables allow the input data to be masked so the device can write to specific bytes. The unwritten bytes retain the previous written value. Table 2–7 summarizes the byte selection.

Table 2–7. Byte Enable for M4K Blocks Notes (1), (2)

byteena[3..0]	datain ×18	datain ×36
[0] = 1	[8..0]	[8..0]
[1] = 1	[17..9]	[17..9]
[2] = 1	–	[26..18]
[3] = 1	–	[35..27]

Notes to Table 2–7:
(1) Any combination of byte enables is possible.
(2) Byte enables can be used in the same manner with 8-bit words, i.e., in ×16 and ×32 modes.

The M4K RAM blocks allow for different clocks on their inputs and outputs. Either of the two clocks feeding the block can clock M4K RAM block registers (`renwe`, address, byte enable, `datain`, and output registers). Only the output register can be bypassed. The eight `labclk` signals or local interconnects can drive the control signals for the A and B ports of the M4K RAM block. LEs can also control the `clock_a`, `clock_b`, `renwe_a`, `renwe_b`, `clr_a`, `clr_b`, `clocken_a`, and `clocken_b` signals, as shown in Figure 2–17.

The R4, R8, C4, C8, and direct link interconnects from adjacent LABs drive the M4K RAM block local interconnect. The M4K RAM blocks can communicate with LABs on either the left or right side through these row resources or with LAB columns on either the right or left with the column resources. Up to 10 direct link input connections to the M4K RAM Block are possible from the left adjacent LABs and another 10 possible from the right adjacent LAB. M4K RAM block outputs can also connect to left and right LABs through 10 direct link interconnects each. Figure 2–18 shows the M4K RAM block to logic array interface.

Table 2–11. M-RAM Combined Byte Selection for ×144 Mode Notes (1), (2)	
byteena[15..0]	**datain ×144**
[0] = 1	[8..0]
[1] = 1	[17..9]
[2] = 1	[26..18]
[3] = 1	[35..27]
[4] = 1	[44..36]
[5] = 1	[53..45]
[6] = 1	[62..54]
[7] = 1	[71..63]
[8] = 1	[80..72]
[9] = 1	[89..81]
[10] = 1	[98..90]
[11] = 1	[107..99]
[12] = 1	[116..108]
[13] = 1	[125..117]
[14] = 1	[134..126]
[15] = 1	[143..135]

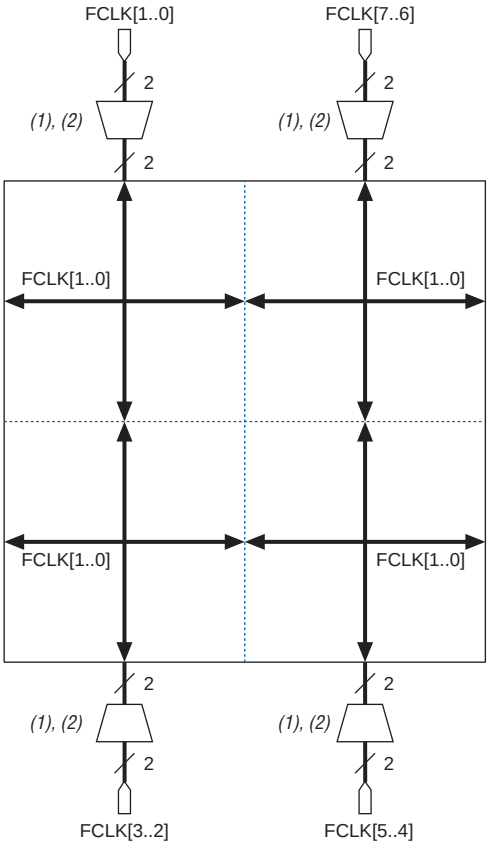
Notes to Tables 2–10 and 2–11:

(1) Any combination of byte enables is possible.

(2) Byte enables can be used in the same manner with 8-bit words, i.e., in ×16, ×32, ×64, and ×128 modes.

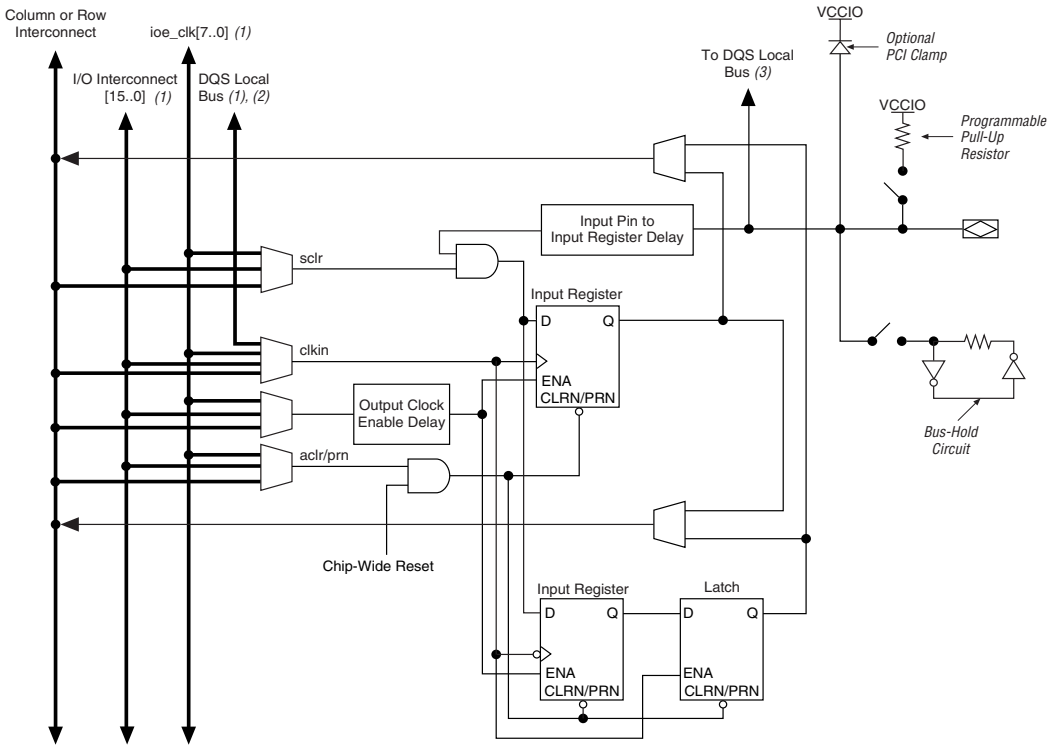
Similar to all RAM blocks, M-RAM blocks can have different clocks on their inputs and outputs. All input registers—`renwe`, `datain`, address, and byte enable registers—are clocked together from either of the two clocks feeding the block. The output register can be bypassed. The eight `labclk` signals or local interconnect can drive the control signals for the A and B ports of the M-RAM block. LEs can also control the `clock_a`, `clock_b`, `renwe_a`, `renwe_b`, `clr_a`, clr_b, `clocken_a`, and `clocken_b` signals as shown in Figure 2–19.

Figure 2–44. EP1S25, EP1S20 & EP1S10 Device Fast Clock Pin Connections to Fast Regional Clocks



Notes to Figure 2–44:
(1) This is a set of two multiplexers.
(2) In addition to the FCLK pin inputs, there is also an input from the I/O interconnect.

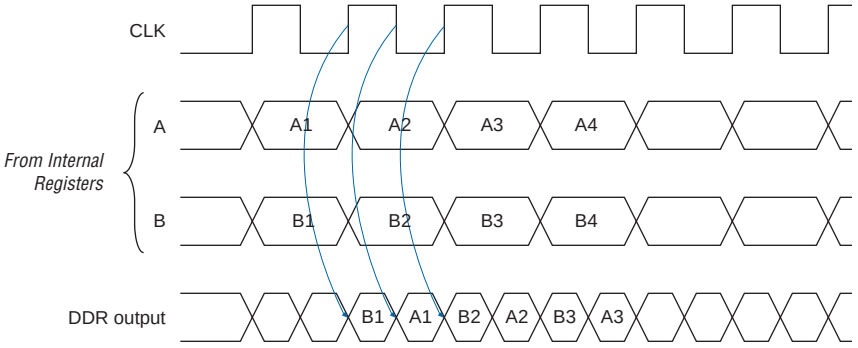
Figure 2–65. Stratix IOE in DDR Input I/O Configuration Note (1)



Notes to Figure 2–65:

(1) All input signals to the IOE can be inverted at the IOE.
(2) This signal connection is only allowed on dedicated DQ function pins.
(3) This signal is for dedicated DQS function pins only.

Figure 2–68. Output Timing Diagram in DDR Mode



The Stratix IOE operates in bidirectional DDR mode by combining the DDR input and DDR output configurations. Stratix device I/O pins transfer data on a DDR bidirectional bus to support DDR SDRAM. The negative-edge-clocked OE register holds the OE signal inactive until the falling edge of the clock. This is done to meet DDR SDRAM timing requirements.

External RAM Interfacing

Stratix devices support DDR SDRAM at up to 200 MHz (400-Mbps data rate) through dedicated phase-shift circuitry, QDR and QDRII SRAM interfaces up to 167 MHz, and ZBT SRAM interfaces up to 200 MHz. Stratix devices also provide preliminary support for reduced latency DRAM II (RLDRAM II) at rates up to 200 MHz through the dedicated phase-shift circuitry.

In addition to the required signals for external memory interfacing, Stratix devices offer the optional clock enable signal. By default the Quartus II software sets the clock enable signal high, which tells the output register to update with new values. The output registers hold their own values if the design sets the clock enable signal low. See Figure 2–64.

To find out more about the DDR SDRAM specification, see the JEDEC web site (**www.jedec.org**). For information on memory controller megafunctions for Stratix devices, see the Altera web site (**www.altera.com**). See *AN 342: Interfacing DDR SDRAM with Stratix & Stratix GX Devices* for more information on DDR SDRAM interface in Stratix. Also see *AN 349: QDR SRAM Controller Reference Design for Stratix & Stratix GX Devices* and *AN 329: ZBT SRAM Controller Reference Design for Stratix & Stratix GX Devices*.

Table 2–27. DQS & DQ Bus Mode Support (Part 2 of 2) Note (1)

Device	Package	Number of ×8 Groups	Number of ×16 Groups	Number of ×32 Groups
EP1S25	672-pin BGA 672-pin FineLine BGA	16 (3)	8	4
	780-pin FineLine BGA 1,020-pin FineLine BGA	20	8	4
EP1S30	956-pin BGA 780-pin FineLine BGA 1,020-pin FineLine BGA	20	8	4
EP1S40	956-pin BGA 1,020-pin FineLine BGA 1,508-pin FineLine BGA	20	8	4
EP1S60	956-pin BGA 1,020-pin FineLine BGA 1,508-pin FineLine BGA	20	8	4
EP1S80	956-pin BGA 1,508-pin FineLine BGA 1,923-pin FineLine BGA	20	8	4

Notes to Table 2–27:

(1) See the *Selectable I/O Standards in Stratix & Stratix GX Devices* chapter in the *Stratix Device Handbook, Volume 2* for V_{REF} guidelines.
(2) These packages have six groups in I/O banks 3 and 4 and six groups in I/O banks 7 and 8.
(3) These packages have eight groups in I/O banks 3 and 4 and eight groups in I/O banks 7 and 8.
(4) This package has nine groups in I/O banks 3 and 4 and nine groups in I/O banks 7 and 8.
(5) These packages have three groups in I/O banks 3 and 4 and four groups in I/O banks 7 and 8.

A compensated delay element on each DQS pin automatically aligns input DQS synchronization signals with the data window of their corresponding DQ data signals. The DQS signals drive a local DQS bus in the top and bottom I/O banks. This DQS bus is an additional resource to the I/O clocks and is used to clock DQ input registers with the DQS signal.

Two separate single phase-shifting reference circuits are located on the top and bottom of the Stratix device. Each circuit is driven by a system reference clock through the `CLK` pins that is the same frequency as the DQS signal. Clock pins `CLK[15..12]p` feed the phase-shift circuitry on the top of the device and clock pins `CLK[7..4]p` feed the phase-shift circuitry on the bottom of the device. The phase-shifting reference circuit on the top of the device controls the compensated delay elements for all 10 DQS pins located at the top of the device. The phase-shifting reference circuit on the bottom of the device controls the compensated delay elements for all 10 DQS pins located on the bottom of the device. All 10 delay elements (DQS signals) on either the top or bottom of the device

Table 2–37. EP1S10, EP1S20 & EP1S25 Device Differential Channels (Part 2 of 2) Note (1)

Device	Package	Transmitter/ Receiver	Total Channels	Maximum Speed (Mbps)	Center Fast PLLs			
					PLL 1	PLL 2	PLL 3	PLL 4
EP1S25	672-pin FineLine BGA 672-pin BGA	Transmitter (2)	56	624 (4)	14	14	14	14
				624 (3)	28	28	28	28
		Receiver	58	624 (4)	14	15	15	14
				624 (3)	29	29	29	29
	780-pin FineLine BGA	Transmitter (2)	70	840 (4)	18	17	17	18
				840 (3)	35	35	35	35
		Receiver	66	840 (4)	17	16	16	17
				840 (3)	33	33	33	33
	1,020-pin FineLine BGA	Transmitter (2)	78	840 (4)	19	20	20	19
				840 (3)	39	39	39	39
		Receiver	78	840 (4)	19	20	20	19
				840 (3)	39	39	39	39

Notes to Table 2–37:

(1) The first row for each transmitter or receiver reports the number of channels driven directly by the PLL. The second row below it shows the maximum channels a PLL can drive if cross bank channels are used from the adjacent center PLL. For example, in the 484-pin FineLine BGA EP1S10 device, PLL 1 can drive a maximum of five channels at 840 Mbps or a maximum of 10 channels at 840 Mbps. The Quartus II software may also merge receiver and transmitter PLLs when a receiver is driving a transmitter. In this case, one fast PLL can drive both the maximum numbers of receiver and transmitter channels.

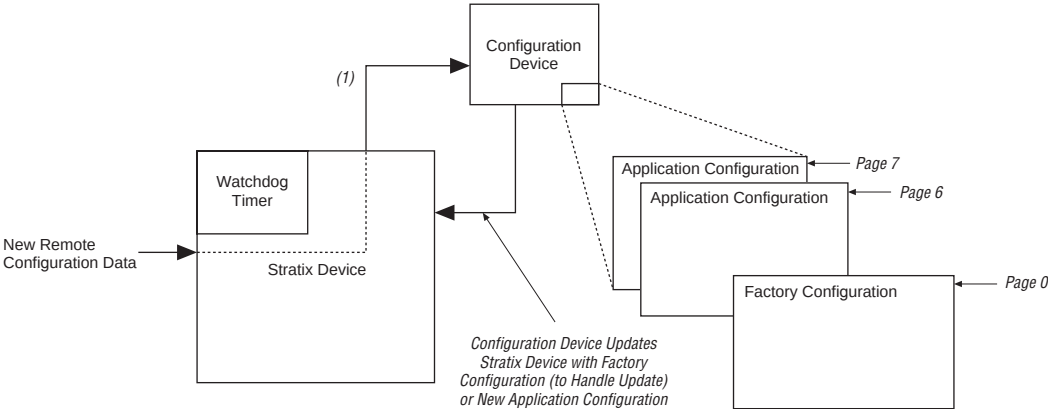
(2) The number of channels listed includes the transmitter clock output (`tx_outclock`) channel. If the design requires a DDR clock, it can use an extra data channel.

(3) These channels span across two I/O banks per side of the device. When a center PLL clocks channels in the opposite bank on the same side of the device it is called cross-bank PLL support. Both center PLLs can clock cross-bank channels simultaneously if, for example, PLL_1 is clocking all receiver channels and PLL_2 is clocking all transmitter channels. You cannot have two adjacent PLLs simultaneously clocking cross-bank receiver channels or two adjacent PLLs simultaneously clocking transmitter channels. Cross-bank allows for all receiver channels on one side of the device to be clocked on one clock while all transmitter channels on the device are clocked on the other center PLL. Crossbank PLLs are supported at full-speed, 840 Mbps. For wire-bond devices, the full-speed is 624 Mbps.

(4) These values show the channels available for each PLL without crossing another bank.

When you span two I/O banks using cross-bank support, you can route only two load enable signals total between the PLLs. When you enable `rx_data_align`, you use both `rxloadena` and `txloadena` of a PLL. That leaves no `loadena` for the second PLL.

Figure 3–2. Stratix Device Remote Update



Note to Figure 3–2:

(1) When the Stratix device is configured with the factory configuration, it can handle update data from EPC16, EPC8, or EPC4 configuration device pages and point to the next page in the configuration device.

Table 4–2. Stratix Device Recommended Operating Conditions (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	*(4)*, *(5)*	3.00 (3.135)	3.60 (3.465)	V
	Supply voltage for output buffers, 2.5-V operation	*(4)*	2.375	2.625	V
	Supply voltage for output buffers, 1.8-V operation	*(4)*	1.71	1.89	V
	Supply voltage for output buffers, 1.5-V operation	*(4)*	1.4	1.6	V
V_I	Input voltage	*(3)*, *(6)*	–0.5	4.0	V
V_O	Output voltage		0	V_{CCIO}	V
T_J	Operating junction temperature	For commercial use	0	85	°C
		For industrial use	–40	100	°C

Table 4–3. Stratix Device DC Operating Conditions Note (7) (Part 1 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
I_I	Input pin leakage current	$V_I = V_{CCIOmax}$ to 0 V *(8)*	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	$V_O = V_{CCIOmax}$ to 0 V *(8)*	–10		10	µA
I_{CC0}	V_{CC} supply current (standby) (All memory blocks in power-down mode)	V_I = ground, no load, no toggling inputs				mA
		EP1S10. V_I = ground, no load, no toggling inputs		37		mA
		EP1S20. V_I = ground, no load, no toggling inputs		65		mA
		EP1S25. V_I = ground, no load, no toggling inputs		90		mA
		EP1S30. V_I = ground, no load, no toggling inputs		114		mA
		EP1S40. V_I = ground, no load, no toggling inputs		145		mA
		EP1S60. V_I = ground, no load, no toggling inputs		200		mA
		EP1S80. V_I = ground, no load, no toggling inputs		277		mA

Table 4–22. SSTL-3 Class I Specifications (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
$V_{IL(AC)}$	Low-level AC input voltage				V_{REF} – 0.4	V
V_{OH}	High-level output voltage	I_{OH} = –8 mA *(3)*	V_{TT} + 0.6			V
V_{OL}	Low-level output voltage	I_{OL} = 8 mA *(3)*			V_{TT} – 0.6	V

Table 4–23. SSTL-3 Class II Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
V_{CCIO}	Output supply voltage		3.0	3.3	3.6	V
V_{TT}	Termination voltage		V_{REF} – 0.05	V_{REF}	V_{REF} + 0.05	V
V_{REF}	Reference voltage		1.3	1.5	1.7	V
$V_{IH(DC)}$	High-level DC input voltage		V_{REF} + 0.2		V_{CCIO} + 0.3	V
$V_{IL(DC)}$	Low-level DC input voltage		–0.3		V_{REF} – 0.2	V
$V_{IH(AC)}$	High-level AC input voltage		V_{REF} + 0.4			V
$V_{IL(AC)}$	Low-level AC input voltage				V_{REF} – 0.4	V
V_{OH}	High-level output voltage	I_{OH} = –16 mA *(3)*	V_{TT} + 0.8			V
V_{OL}	Low-level output voltage	I_{OL} = 16 mA *(3)*			V_{TT} – 0.8	V

Table 4–24. 3.3-V AGP 2× Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
V_{CCIO}	Output supply voltage		3.15	3.3	3.45	V
V_{REF}	Reference voltage		0.39 × V_{CCIO}		0.41 × V_{CCIO}	V
V_{IH}	High-level input voltage *(4)*		0.5 × V_{CCIO}		V_{CCIO} + 0.5	V
V_{IL}	Low-level input voltage *(4)*				0.3 × V_{CCIO}	V
V_{OH}	High-level output voltage	I_{OUT} = –0.5 mA	0.9 × V_{CCIO}		3.6	V
V_{OL}	Low-level output voltage	I_{OUT} = 1.5 mA			0.1 × V_{CCIO}	V

Table 4–25. 3.3-V AGP 1× Specifications (Part 1 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
V_{CCIO}	Output supply voltage		3.15	3.3	3.45	V
V_{IH}	High-level input voltage *(4)*		0.5 × V_{CCIO}		V_{CCIO} + 0.5	V
V_{IL}	Low-level input voltage *(4)*				0.3 × V_{CCIO}	V

Internal Timing Parameters

Internal timing parameters are specified on a speed grade basis independent of device density. Tables 4–37 through 4–42 describe the Stratix device internal timing microparameters for LEs, IOEs, TriMatrix™ memory structures, DSP blocks, and MultiTrack interconnects.

Table 4–37. LE Internal Timing Microparameter Descriptions

Symbol	Parameter
t_{SU}	LE register setup time before clock
t_{H}	LE register hold time after clock
t_{CO}	LE register clock-to-output delay
t_{LUT}	LE combinatorial LUT delay for data-in to data-out
t_{CLR}	Minimum clear pulse width
t_{PRE}	Minimum preset pulse width
t_{CLKHL}	Register minimum clock high or low time. The maximum core clock frequency can be calculated by $1/(2 \times t_{CLKHL})$.

Table 4–38. IOE Internal Timing Microparameter Descriptions

Symbol	Parameter
t_{SU_R}	Row IOE input register setup time
t_{SU_C}	Column IOE input register setup time
t_{H}	IOE input and output register hold time after clock
t_{CO_R}	Row IOE input and output register clock-to-output delay
t_{CO_C}	Column IOE input and output register clock-to-output delay
$t_{PIN2COMBOUT\_R}$	Row input pin to IOE combinatorial output
$t_{PIN2COMBOUT\_C}$	Column input pin to IOE combinatorial output
$t_{COMBIN2PIN\_R}$	Row IOE data input to combinatorial output pin
$t_{COMBIN2PIN\_C}$	Column IOE data input to combinatorial output pin
t_{CLR}	Minimum clear pulse width
t_{PRE}	Minimum preset pulse width
t_{CLKHL}	Register minimum clock high or low time. The maximum I/O clock frequency can be calculated by $1/(2 \times t_{CLKHL})$. Performance may also be affected by I/O timing, use of PLL, and I/O programmable settings.

Stratix External I/O Timing

These timing parameters are for both column IOE and row IOE pins. In EP1S30 devices and above, you can decrease the t_{SU} time by using the FPLLCLK, but may get positive hold time in EP1S60 and EP1S80 devices. You should use the Quartus II software to verify the external devices for any pin.

Tables 4–55 through 4–60 show the external timing parameters on column and row pins for EP1S10 devices.

Table 4–55. EP1S10 External I/O Timing on Column Pins Using Fast Regional Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.238		2.325		2.668		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.240	4.549	2.240	4.836	2.240	5.218	NA	NA	ns
t_{XZ}	2.180	4.423	2.180	4.704	2.180	5.094	NA	NA	ns
t_{ZX}	2.180	4.423	2.180	4.704	2.180	5.094	NA	NA	ns

Table 4–56. EP1S10 External I/O Timing on Column Pins Using Regional Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max			
t_{INSU}	1.992		2.054		2.359		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.395	4.795	2.395	5.107	2.395	5.527	NA	NA	ns
t_{XZ}	2.335	4.669	2.335	4.975	2.335	5.403	NA	NA	ns
t_{ZX}	2.335	4.669	2.335	4.975	2.335	5.403	NA	NA	ns
$t_{INSUPLL}$	0.975		0.985		1.097		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA	NA	ns
$t_{OUTCOPLL}$	1.262	2.636	1.262	2.680	1.262	2.769	NA	NA	ns
t_{XZPLL}	1.202	2.510	1.202	2.548	1.202	2.645	NA	NA	ns
t_{ZXPLL}	1.202	2.510	1.202	2.548	1.202	2.645	NA	NA	ns

Definition of I/O Skew

I/O skew is defined as the absolute value of the worst-case difference in clock-to-out times (t_{CO}) between any two output registers fed by a common clock source.

I/O bank skew is made up of the following components:

- Clock network skews: This is the difference between the arrival times of the clock at the clock input port of the two IOE registers.
- Package skews: This is the package trace length differences between (I/O pad A to I/O pin A) and (I/O pad B to I/O pin B).

Figure 4–5 shows an example of two IOE registers located in the same bank, being fed by a common clock source. The clock can come from an input pin or from a PLL output.

Figure 4–5. I/O Skew within an I/O Bank

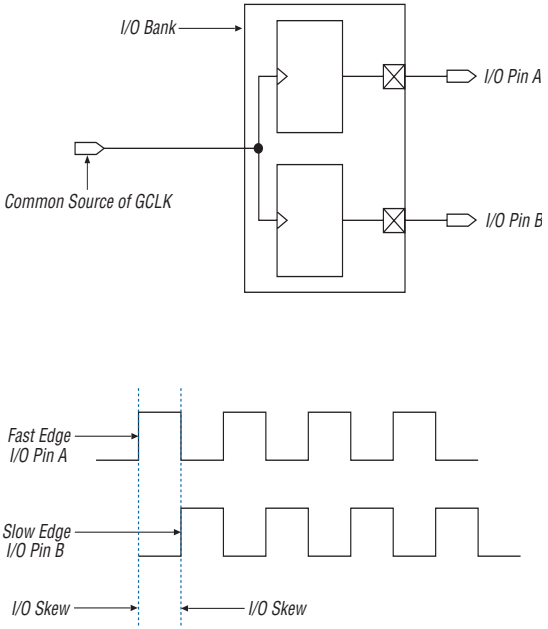


Table 4–125. High-Speed I/O Specifications for Flip-Chip Packages (Part 3 of 4) *Notes (1), (2)*

Symbol	Conditions	-5 Speed Grade			-6 Speed Grade			-7 Speed Grade			-8 Speed Grade			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
SW	PCML (*J* = 4, 7, 8, 10)	750			750			800			800			ps
	PCML (*J* = 2)	900			900			1,200			1,200			ps
	PCML (*J* = 1)	1,500			1,500			1,700			1,700			ps
	LVDS and LVPECL (*J* = 1)	500			500			550			550			ps
	LVDS, LVPECL, HyperTransport technology (*J* = 2 through 10)	440			440			500			500			ps
Input jitter tolerance (peak-to-peak)	All			250			250			250			250	ps
Output jitter (peak-to-peak)	All			160			160			200			200	ps
Output t_{RISE}	LVDS	80	110	120	80	110	120	80	110	120	80	110	120	ps
	HyperTransport technology	110	170	200	110	170	200	120	170	200	120	170	200	ps
	LVPECL	90	130	150	90	130	150	100	135	150	100	135	150	ps
	PCML	80	110	135	80	110	135	80	110	135	80	110	135	ps
Output t_{FALL}	LVDS	80	110	120	80	110	120	80	110	120	80	110	120	ps
	HyperTransport technology	110	170	200	110	170	200	110	170	200	110	170	200	ps
	LVPECL	90	130	160	90	130	160	100	135	160	100	135	160	ps
	PCML	105	140	175	105	140	175	110	145	175	110	145	175	ps

Table 4–125. High-Speed I/O Specifications for Flip-Chip Packages (Part 4 of 4) Notes (1), (2)

Symbol	Conditions	-5 Speed Grade			-6 Speed Grade			-7 Speed Grade			-8 Speed Grade			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
t_{DUTY}	LVDS (J = 2 through 10)	47.5	50	52.5	47.5	50	52.5	47.5	50	52.5	47.5	50	52.5	%
	LVDS (J =1) and LVPECL, PCML, HyperTransport technology	45	50	55	45	50	55	45	50	55	45	50	55	%
t_{LOCK}	All			100			100			100			100	µs

Notes to Table 4–125:

(1) When J = 4, 7, 8, and 10, the SERDES block is used.

(2) When J = 2 or J = 1, the SERDES is bypassed.

Table 4–126. High-Speed I/O Specifications for Wire-Bond Packages (Part 2 of 2)

Symbol	Conditions	-6 Speed Grade			-7 Speed Grade			-8 Speed Grade			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
SW	PCML (J = 4, 7, 8, 10) only	800			800			800			ps
	PCML (J = 2) only	1,200			1,200			1,200			ps
	PCML (J = 1) only	1,700			1,700			1,700			ps
	LVDS and LVPECL (J = 1) only	550			550			550			ps
	LVDS, LVPECL, HyperTransport technology (J = 2 through 10) only	500			500			500			ps
Input jitter tolerance (peak-to-peak)	All			250			250			250	ps
Output jitter (peak-to-peak)	All			200			200			200	ps
Output t_{RISE}	LVDS	80	110	120	80	110	120	80	110	120	ps
	HyperTransport technology	120	170	200	120	170	200	120	170	200	ps
	LVPECL	100	135	150	100	135	150	100	135	150	ps
	PCML	80	110	135	80	110	135	80	110	135	ps
Output t_{FALL}	LVDS	80	110	120	80	110	120	80	110	120	ps
	HyperTransport	110	170	200	110	170	200	110	170	200	ps
	LVPECL	100	135	160	100	135	160	100	135	160	ps
	PCML	110	145	175	110	145	175	110	145	175	ps
t_{DUTY}	LVDS (J = 2 through10) only	47.5	50	52.5	47.5	50	52.5	47.5	50	52.5	%
	LVDS (J =1) and LVPECL, PCML, HyperTransport technology	45	50	55	45	50	55	45	50	55	%
t_{LOCK}	All			100			100			100	µs

Table 4–132. Fast PLL Specifications for -7 Speed Grades (Part 2 of 2)

Symbol	Parameter	Min	Max	Unit
t_{JITTER}	Period jitter for DIFFIO clock out *(6)*		*(5)*	ps
t_{LOCK}	Time required for PLL to acquire lock	10	100	µs
m	Multiplication factors for *m* counter *(7)*	1	32	Integer
*l*0, *l*1, *g*0	Multiplication factors for *l*0, *l*1, and *g*0 counter *(7)*, *(8)*	1	32	Integer
t_{ARESET}	Minimum pulse width on `areset` signal	10		ns

Table 4–133. Fast PLL Specifications for -8 Speed Grades (Part 1 of 2)

Symbol	Parameter	Min	Max	Unit
f_{IN}	`CLKIN` frequency *(1)*, *(3)*	10	460	MHz
f_{INPFD}	Input frequency to PFD	10	500	MHz
f_{OUT}	Output frequency for internal global or regional clock *(4)*	9.375	420	MHz
f_{OUT_DIFFIO}	Output frequency for external clock driven out on a differential I/O data channel	*(5)*	*(5)*	MHz
f_{VCO}	VCO operating frequency	300	700	MHz
t_{INDUTY}	`CLKIN` duty cycle	40	60	%
$t_{INJITTER}$	Period jitter for `CLKIN` pin		±200	ps
t_{DUTY}	Duty cycle for `DFFIO` 1× `CLKOUT` pin *(6)*	45	55	%
t_{JITTER}	Period jitter for DIFFIO clock out *(6)*		*(5)*	ps
t_{LOCK}	Time required for PLL to acquire lock	10	100	µs
m	Multiplication factors for *m* counter *(7)*	1	32	Integer
*l*0, *l*1, *g*0	Multiplication factors for *l*0, *l*1, and *g*0 counter *(7)*, *(8)*	1	32	Integer

5. Reference & Ordering Information

S51005-2.1

Software

Stratix® devices are supported by the Altera® Quartus® II design software, which provides a comprehensive environment for system-on-a-programmable-chip (SOPC) design. The Quartus II software includes HDL and schematic design entry, compilation and logic synthesis, full simulation and advanced timing analysis, SignalTap® II logic analyzer, and device configuration. See the *Design Software Selector Guide* for more details on the Quartus II software features.

The Quartus II software supports the Windows XP/2000/NT/98, Sun Solaris, Linux Red Hat v7.1 and HP-UX operating systems. It also supports seamless integration with industry-leading EDA tools through the NativeLink® interface.

Device Pin-Outs

Stratix device pin-outs can be found on the Altera web site **(www.altera.com).**

Ordering Information

Figure 5–1 describes the ordering codes for Stratix devices. For more information on a specific package, see the *Package Information for Stratix Devices* chapter.